

Supercontinuum generation with femtosecond optical pulse compression in silicon photonic crystal fbers at 2500 nm

Ashkan Ghanbari1 · Alireza Kashaninia1 · Ali Sadr2 · Hamed Saghaei3

Received: 24 July 2018 / Accepted: 29 September 2018 / Published online: 30 October 2018 © Springer Science+Business Media, LLC, part of Springer Nature 2018

Abstract

In this paper, femtosecond optical pulses compression and supercontinuum generation in a triangular silicon photonic crystal fber at 2500 nm are investigated. A region of large minimum anomalous group velocity dispersion, negligible higher order dispersions and unique nonlinearity of silicon are used to demonstrate compression of 100 fs initial input optical pulses to 2.5 fs and ultra-broadband supercontinuum generation with very low input pulse energy over short distances of the fber.

Keywords Soliton · Compression · Dispersion · Photonic · Crystal

1 Introduction

According to the appearance of the applications in several felds of the sciences, researches and technologies, ultrashort optical pulses generation has been considered an interesting topic among scientists. The accessibility of these ultrashort laser pulses has opened numerous regions of applications in many applicable optical felds, such as spectroscopy, nonlinear optics, Optical Coherent Tomography (OCT), precious optical measurement of optical frequencies, material process and etc. (Ferreira [2011\)](#page-10-0). Ultrashort femtosecond laser pulses have been generated either from diferent optical laser sources such as Ti:sapphire

 \boxtimes Alireza Kashaninia ali.kashaniniya@iauctb.ac.ir

> Ashkan Ghanbari ashkan.ghanbari@iauctb.ac.ir

Ali Sadr sadr@iust.ac.ir

Hamed Saghaei h.saghaei@iaushk.ac.ir

- ¹ Department of Electrical Engineering, Faculty of Engineering, Central Tehran Branch, Islamic Azad University, Tehran, Iran
- ² Faculty of Electrical and Electronics Engineering, Iran University of Science and Technology (IUST), Tehran, Iran
- ³ Department of Electrical Engineering, Shahrekord Branch, Islamic Azad University, Shahrekord, Iran

oscillators (800 nm), Er:fber laser (1550 nm), Nd:YAG lasers (1064 nm) (Ghanbari et al. 2017) and Cr⁺²:ZnSe laser (2500 nm) (Cizmeciyan et al. [2013\)](#page-10-1) or by spectral extending of the optic pulse and post compression using dispersion compensating fundaments (Mohebbi [2008\)](#page-11-1).

Ultrashort optical pulses generation directly from laser sources require more complex activity such as, cavity and dispersion compensating mirrors designs and also use of enhanced optical pulses with energy in micro joule ranges (Ferreira [2011;](#page-10-0) Mohebbi [2008](#page-11-1)). One of the most widely used techniques for the generation of ultrashort optical pulses uses higher order solitons which are organized in a fber. This compression method named soliton-efect and has been used in many researches (Ferreira [2011\)](#page-10-0).

Recently, photonic crystal fbers have been attracted the attention of many scientists and researchers for their highly precious applications in lasers, nonlinear optics, dispersion compensation, optical amplifers, optical sensors and etc. (Ferreira [2011](#page-10-0); Cizmeciyan et al. [2013;](#page-10-1) Mohebbi [2008](#page-11-1); Saghaei [2015](#page-11-2)) and also several types of fabricating with variable materials have been reported so far (Saghaei [2015;](#page-11-2) Ghanbari et al. [2017;](#page-11-0) Li and Yaman [2010;](#page-11-3) Leong et al. [2006](#page-11-4); Bowmans et al. [2003](#page-10-2)). Because of the presence of air holes in the various lattice structures of photonic crystal fbers, acquiring various optical properties such as Large Mode Area (LMA), high nonlinearity, adjustable zero dispersion and etcetera become possible in comparison with conventional optical fbers (Ghanbari et al. [2017;](#page-11-0) Li and Yaman [2010](#page-11-3); Ghanbari [2012](#page-10-3)). Among the items mentioned above, the combination of boosted nonlinearity and engineered dispersion is the one which makes the solitonefects optical pulses compression and ultra-broadband supercontinuum generation possible in a broad regions of wavelengths from visible to infrared in diferent kinds of PCFs (Saghaei [2015;](#page-11-2) Ghanbari et al. [2014](#page-11-5), [2017](#page-11-0); Ghanbari [2012\)](#page-10-3). Photonic crystal fbers can be made from diferent optical materials such as silica (Leong et al. [2006](#page-11-4)), fuoride magnesium (Ghanbari et al. [2017](#page-11-0)), chalcogenide glasses (Saghaei [2015\)](#page-11-2) and also silicon (Li and Yaman [2010](#page-11-3)). Today silicon is known as one of the most important and well known materials for fabrication of optoelectronic instruments (Mohebbi [2008;](#page-11-1) Li and Yaman [2010](#page-11-3)). Recently, silicon photonic crystal fbers have been fabricated by a special method named "magnesium thermic method" with the ability to maintain the Nano scales dimensions of the related silicon fbers (Li and Yaman [2010\)](#page-11-3). Based on our researches, silicon has larger nonlinear refractive index than silica, chalcogenide glasses and also fuoride magnesium (Saghaei [2015;](#page-11-2) Ghanbari et al. [2017;](#page-11-0) Bowmans et al. [2003\)](#page-10-2). Finally, this valuable nonlinear refractive index results in obtaining higher nonlinear coefficient and subsequently lower required input pulse energy for nonlinear applications such as optical compression or supercontinuum generation.

In this paper, we focused on designing a novel structure of photonic crystal fber consisting of a silicon core surrounded by fve rings of air holes embedded in a triangular lattice in the cladding and we also used the soliton-efect method for compression of femtosecond optical pulses and ultra-broadband supercontinuum generation.

2 Dispersion of silicon photonic crystal fbers

Dispersion is one of the most important linear parameters that afects the short and ultrashort pulses propagation which causes optical pulses broadening in the time domain (Mohebbi [2008](#page-11-1)). By changing the structural parameters of photonic crystal fbers such as wavelengths (λ), hole pitch (Λ) and normalized air hole diameter ($\frac{d}{\Lambda}$), PCF's dispersion can change. Also Shifting zero dispersion points in photonic crystal fbers are possible by dependency of group velocity dispersion (GVD) to structural parameters of PCFs (Ferreira [2011;](#page-10-0) Saghaei [2015](#page-11-2); Ghanbari et al. [2017\)](#page-11-0).

As seen in Fig. [1,](#page-2-0) we considered a triangular lattice silicon PCF with fve rings of air holes in the cladding. In the center an air hole is deleted making a central high index defect acting as the PCF core. In order to calculate propagation constant (β) for the proposed silicon PCF, among all the accurate available techniques, we selected one of the well-known numerical methods named Finite Diference Time Domain (FDTD) combined with the perfectly matched layer (PML) as absorbing boundaries (Saghaei [2015](#page-11-2); Ghanbari et al. [2017](#page-11-0)). The second and higher order dispersions of the fber can be calculated by taking the frst, second and higher orders derivative of the propagation constant with respect to angular frequency as following equation respectively (Ferreira [2011](#page-10-0); Mohebbi [2008](#page-11-1)). Where dependency of the silicon material has been also applied into the calculations (Ghanbari [2012](#page-10-3); Lin and Agrawal [2007](#page-11-6)),

$$
\beta_n = \frac{\partial \beta_{n-1}}{\partial \omega} \quad n = 2, 3, 4, \dots \tag{1}
$$

In Fig. [2](#page-3-0), we have shown the GVD as a function of wavelength in the short wavelength infrared (SWIR) and mid infrared (MIR) regions of the spectrum for the largest possible value of normalized air hole size $\left(\frac{d}{\Lambda}\right) = 0.8$ and different values of pitches (Λ). As seen in Fig. [2,](#page-3-0) there is a nearly fat and minimum region of negative second order dispersion (GVD) which by changing the hole pitch (A) is shifted to higher wavelengths. So by choosing the proper values of $A = 0.7$ µm and $d/_{A} = 0.8$, this negative and nearly flat region of GVD can be centered at 2500 nm wavelength. The importance of nearly fat region in supercontinuum generation and soliton-efect pulse compression contributes to achieving negligible higher order dispersions.

When we consider the propagation of ultrashort optical pulses with femtosecond durations, the higher order dispersions (HODs) (such as third, fourth, ffth and etc.) will be of great importance and must be included in the wave equation. In Fig. [3](#page-3-1) we have shown the third (TOD), fourth (FOD) and ffth order dispersions of the fber as a function of wavelength for $d/_{\Lambda}$ = 0.8 and Λ = 0.7 µm. This figure clearly shows that in the similar region of wavelengths where there is a large minimum and nearly fat negative second order dispersion, the values of higher order dispersions in the novel designed silicon PCF will be

Fig. 1 Silicon PCF schematic

Fig. 3 Up to fifth order dispersions of silicon PCF as a function of wavelength for $\Lambda = 0.7 \mu m$ and $d_{A}^{7} = 0.8$

negligible compared to the value of GVD, which are ideally needed for supercontinuum generation and soliton-efect compression. But it is noteworthy that although these higher order dispersions values are small at 2500 nm wavelength, they should be considered in the wave equation. Another important linear parameter which can afect the propagated pulse inside the fiber is fiber loss $(L_t = L_c + L_m)$ (Saghaei [2015;](#page-11-2) Ghanbari et al. [2017\)](#page-11-0). Total loss of the fber includes material loss and confnement loss respectively. Based on our research and simulation results, the silicon PCF confnement Loss could be negligible compared to the material loss of silicon according to presence of air holes in the cladding. So, for the rest of the paper we considered the silicon material loss with the value of 8 db/m (Luther et al. [2013\)](#page-11-7) at the central wavelength of 2500 nm in the accounts.

3 Soliton‑efect compression in silicon photonic crystal fbers

In this kind of optical pulse compression mechanism, the waveguide, itself, acts as a compressor. In fact, soliton-efect optical pulse compression occurs through the propagation of higher order solitons in the anomalous GVD regions of the fber and interact with selfphase modulation (SPM). In this case by choosing the appropriate length of the fber where the pulse goes under periodic compressing, we can select the ultrashort output pulse.

Figure [4](#page-4-0), shows the efective areas of silicon designed PCF for the structure parameters of $\Lambda = 0.7$ μ m, $d / \Lambda = 0.8$ and $\Lambda = 0.95$ μ m, $d / \Lambda = 0.8$ respectively. The Combination of unique nonlinear refractive index of silicon (n2) with a small efective area, fnally results in higher nonlinear index ($\gamma \propto \frac{1}{A_{eff}} \propto n_2$). Smaller effective area can be achieved by

designing photonic crystal fibers with smaller pitches (Λ). Also smaller effective area leads to a shorter nonlinear length (L_M) . Ultimately, all of the items above contribute to a conspicuous reduction in required energy for PCF's nonlinear applications. As seen in Fig. [4](#page-4-0), the effective area for the proposed silicon PCF with the structure parameters of $\Lambda = 0.7$ µm and $d/_{\Lambda} = 0.8$ is calculated to be 0.52 μ m² at 2500 nm wavelength which is much smaller than the effective area of proposed PCF with the structure parameters of $\Lambda = 0.95 \mu m$ and $d/_{\Lambda} = 0.8$ at 3500 nm wavelength which is calculated to be 1 µm².

The Generalized Nonlinear Schrödinger Equation which describes the propagation of optical pulses through fbers can be written in the following normalized form (Saghaei [2015;](#page-11-2) Ghanbari et al. [2014](#page-11-5), [2017](#page-11-0); Ghanbari [2012](#page-10-3)),

$$
\frac{\partial U}{\partial \xi} = \overbrace{-\frac{isgn(\beta_2)}{2} \frac{\partial^2 U}{\partial \tau^2} + \frac{\beta_3}{6|\beta_2|T_0} \frac{\partial^3 U}{\partial \tau^3} + i \frac{\beta_4}{24|\beta_2|T_0^2} \frac{\partial^4 U}{\partial \tau^4} - \frac{\beta_5}{120|\beta_2|T_0^3} \frac{\partial^5 U}{\partial \tau^5} + \dots + L_D \alpha_L / 2U + iN^2 \underbrace{(|U|^2 U)^2}_{SPM} + iN^2 \underbrace{(|U|^2 U)^2}_{SPM} + \underbrace{\frac{i}{\omega_0 T_0}}_{Self - steepening} \underbrace{\frac{\partial (|U|^2 U)}{\partial \tau}}_{Nonlinear - effects} - \underbrace{U / T_0 f_R \int_0^\infty th_R(t) dt \frac{\partial |U|^2}{\partial \tau}}_{RAMM} - \underbrace{N^2 \alpha_{TPA}}_{PAA} / 2\gamma A_{eff} U |U|^2}_{TPA} \tag{2}
$$

Fig. 4 Efective area of the fundamental mode for a silicon PCF

where $\tau = T/T_0$ is the normalized time, T0 states the initial pulse width of optical pulses $(T_{FWHM} = 1.76T_0)$, T_{FWHM} states full width at half maximum of the optical pulse, and $U(z, \tau) = A(z, \tau) \sqrt{\sqrt{P_0}}$ is the normalized pulse amplitude, P0 is the peak power of input pulse, $\alpha(m^{-1})$ is linear loss coefficient, β_2 , β_3 , β_4 , β_5 are GVD, TOD, FOD and Fifth order dispersions respectively. ω_0 is the central angular frequency, $\frac{1}{\omega_0 T_0}$ is responsible for selfsteepening, f_R is Raman constant and is calculated 0.04 for silicon material (Ghanbari [2012;](#page-10-3) Luther et al. [2013](#page-11-7); Lin and Agrawal [2007\)](#page-11-6). $h_R(t)$ is Raman Function and can be calculated by definition of $\tau_1 = 10$ fs and $\tau_2 = 3$ ps for silicon material in the following formula (Mohebbi [2008\)](#page-11-1),

$$
h_R(t) = \frac{\tau_1^2 + \tau_2^2}{\tau_1 \tau_2^2} e^{\frac{-t}{\tau_2}} \sin(\frac{t}{\tau_1})
$$
 (3)

 N^2 is the order of soliton and defined as,

$$
N^2 = \frac{\gamma P_0 T_0^2}{|\beta_2|} \tag{4}
$$

where, γ states the nonlinear coefficient defined by Eq. [\(4](#page-5-0)),

$$
\gamma = \frac{n_2 \omega_0}{c A_{\text{eff}}} \tag{5}
$$

where $n_2 \left(\frac{m^2}{W}\right)$) is the nonlinear refractive index with the value of $3.3 \times 10^{-18} \text{ m}^2/\text{W}$ for silicon at operational wavelength of 2500 nm (Mohebbi [2008;](#page-11-1) Yue et al. [2012\)](#page-11-8), *Aeff* is the

Fig. 5 Output compressed pulse at the wavelength of 2500 nm and propagation distance of 0.5 mm. Input pulse is also shown

 $\circled{2}$ Springer

effective area of the PCF, c shows the speed of light and finally $\xi = \frac{z}{L_D}$ is the normalized distance of the fiber, Where L_D is the dispersion length defined by the following equation,

$$
L_D = \frac{T_0^2}{|\beta_2|} \tag{6}
$$

The longer Dispersion length is, the shorter compressed pulse goes. It means that by choosing proper PCF fundamental parameters, we can make the second order dispersion (β_2) minimum at the wavelength of 2500 nm which leads to longer dispersion length (corresponds to a longer soliton period) compared to shorter wavelengths. In this manner, the condition of L_D >> L_{NI} is satisfied which finally results in shorter compressed pulse. Also it is noteworthy that because of the lower magnitude of Raman response in silicon material compared to magnitude of another nonlinear efects such as SPM and self-steepening, the Raman Efect can be negligible, however, we have included it in the propagation equation. α_{TPA} is responsible for two photon absorption which limits the nonlinear effects of the silicon fbers. This important item appears for the wavelengths below 2300 nm in silicon material (Ghanbari [2012;](#page-10-3) Mohebi and Khormai [2011\)](#page-11-9). So, by choosing the operational wavelength above the mentioned wavelength, this efect will be eliminated.

The widely used Symmetrized Split-Step Fourier Method (S-SSFM) is applied to simulate the Generalized Nonlinear Schrödinger Equation (GNLSE). We considered $\Lambda = 0.7$ µm and $d/_{\Lambda} = 0.8$ for a silicon photonic crystal fiber structure and used a 100 fs

Fig. 6 Simulated 2D plot of the spectra evolution at discrete locations along the silicon PCF with the input power of 846 W

input pulse at a pump wavelength of 2500 nm. The application of GVD, TOD, FOD and ffth-order order dispersions, Self-Phase Modulation (SPM), linear loss, Self-Steepening (SS) and Raman Efect in Generalized Nonlinear Schrödinger Equation (GNLSE) simulation, yields the shortest compressed pulse of 2.5 fs which is shown in Fig. [5.](#page-5-1) This is due to the motivation of a higher order soliton of order $N=9.5$ for a peak power of $P_0 = 846$ W, and large nonlinear coefficient of γ =16.0 (W⁻¹ m⁻¹) in the propagation distance of $z = 0.5$ mm. The spectra evolution of propagated optical pulse over 0.01 m of the proposed silicon PCF is shown in Fig. [6](#page-6-0). This fgure clearly shows the ultra-broadband supercontinuum generation with the total bandwidth of 3600 nm in a way which covers near infrared to mid infrared regions of the spectrum. This fact is equivalent to extending the wavelength range from 1800 to 5400 nm. Wider supercontinuum spectra with the total bandwidth of 4100 nm can also be generated in the same distances of the PCF with an increase in input power to 1350 W which is shown in Fig. [7.](#page-7-0) In this case, supercontinuum spectra have been propagated with an increase of about 500 nm bandwidth compared to the previous one.

3.1 Comparison between proposed PCF characteristics with other works

In following part, widespread comparisons between our novel designed silicon PCF's structural characteristics and propagation characteristics with previous works are presented in the forms of Tables [1](#page-8-0) and [2.](#page-9-0)

Fig. 7 Simulated 2D plot of the spectra evolution at discrete locations along the silicon PCF with input power of 1350 W

Table 2 Compasrison between porposed PCF propagation characteristics and other works

Table [1](#page-8-0) is allocated to our proposed PCF's structure characteristics and Table [2](#page-9-0) is allocated to propagation characteristics of the designed fber. Comparing the parameters clearly indicate that, the silicon designed PCF in comparison with other designs shows more ideal situation in nonlinear applications especially in supercontinuum generation and solitonefect optical pulses compression. Our designed PCF illustrates a large minimum negative GVD and negligible higher order dispersions (HODs) values in addition to a unique nonlinear coefficient in comparison with other works. Consequently, these valuable features result in enhancing the quality of output compressed pulses, ultra-broadband supercontinuum generation and also a drastic decrease in required energy for nonlinear applications.

4 Conclusion

In this paper, for the frst time, we numerically investigated the soliton-efect compression of femtosecond optical pulses and supercontinuum generation in a novel designed silicon PCF in the near mid infrared (NIR) to mid infrared (MIR) regions of the spectrum. It was shown that by fxing the fundamental parameters of the PCF, we can concentrate a large negative minimum and nearly fat region of GVD at needed wavelengths and fnally calculate the negligible higher-order dispersions which are always desired for efficient ultrabroadband supercontinuum generation and femtosecond optical pulses compression. We illustrated that, by using a 100 fs input pulse with subnanojoule energy of 169 pJ (corresponds to peak power of 846 W), a compressed pulse of 2.5 fs and ultra-broadband supercontinuum with the total bandwidth of 3600 nm can be generated for a silicon PCF with considering, $\Lambda = 0.7$ µm and $d/_{\Lambda} = 0.8$ at the operational wavelength of 2500 nm and the propagation distance of 0.5 mm. Also it was shown that, by increasing the strength of input power to 1350 W, ultra-broadband supercontinuum with the total band width of 4100 nm can be formed in the similar distances of the fber.

References

- Ahamad, R.: Mid infrared super-continuum generation in photonic crystal fbers. MSc Thesis, CzechTechnical University (2016)
- Anitha, P., Manimegalai, A.: Ultra short pulse generation at 1550 nm using a tapered PCF. Int. J. Comput. Appl. **74**(7), 11–13 (2013)
- Bowmans, G., Bigot, L., Lopez, F., Douay, M.: Fabrication and characterization of an all solid 2D photonic band gap fber with a low loss region around 1550nm. Opt. Exp **13**(21), 8452–8459 (2003)
- Cerif, R., Zghal, M.: Nonlinear phenomena ultra-wide band radiation in a photonic crystal fber. J. Opt. **26**(17), 1–7 (2011)
- Cizmeciyan, M.N., Kim, J.W., Bae, S., Hong, B.H., Routermund, F., Sennarouglu, A.: Graphene modelocked femtosecond cr:znse at 2500 nm. JOSA **38**(3), 341–343 (2013)
- Dimitre, G.O., Hensley, J., Geata, A.L., Gallagher, M.T.: Soliton pulse compression in photonic band gap fbers. Opt. Exp. **13**(16), 6153–6159 (2005)
- Diuf, M., Salem, A.B., Cherif, R., Saghaei, H.: Super fat coherent supercontinuum source in AS38.8Se61.2 chalcogenide photonic crystal fber with all normal dispersion engineering at very low input energy. Appl. Opt. **56**(2), 163–169 (2017)
- Ferreira, M.F.S.: Nonlinear Efects in Optical Fibers. Wiley, Hoboken (2011)
- Ghanbari, A.: Femtosecond optical pulses compression by use of photonic crystal fbers. M.Sc. Thesis, Islamic Azad University of Qazvin (2012)
- Ghanbari, A., Sadr, A., Nikoo, M.: Maximization of compression factor and bandwidth of femtosecond optical pulses by use of frequency chirping in photonic crystal fbers. TJEE **43**(2), 32–41 (2013)
- Ghanbari, A., Sadr, A., Tathesari, H.: Modeling photonic crystal fibers for efficient soliton effect compression pf femtosecond optical pulses at 850nm. Arab. J. Sci. Eng. **39**(5), 3917–3923 (2014)
- Ghanbari, A., Kashani Nia, A., Sadr, A.: Square lattice elliptical core photonic crystal fber soliton-efect compressor at 1550 nm. JCE **4**(1), 29–40 (2015)
- Ghanbari, A., Kashani Nia, A., Sadr, A., Saghaei, H.: Supercontinuum generation for optical coherence tomography using magnesium fuoride photonic crystal fber. Optik **140**(114), 545–554 (2017)
- Leong, J.Y.Y., Asimakis, S., Polleti, F., Petropoulous, P., Feng, X., Moore, R., Frampton, K., Ebendorff-Hedepriem, H., Richardson, D.J.: Novel Fabrication Method of Highly-Nonlinear Silica Holey Fibers, pp. 21–25. CLEO, Callifornia (2006)
- Li, G., Yaman, F.: *Silicon Photonic Fiber and Method of Manufacture*, No. 0092141. United States (US) Patent Application Publication (2010)
- Lin, L.Y.Q., Agrawal, G.P.: Soliton fssion and supercontinuum generation in silicon waveguides. Opt. Lett. **32**(4), 391–394 (2007)
- Luther, B., Kuyken, B., Yu, I., Ma, P., Gai, X., Madden, S., Baets, R.: Nonlinear absorption in silicon at mid-infrared wavelengths. In: JOSA Conference Paper (2013)
- Maggie, C.Y., Chen, R.T.: One stage pulse compression at 1554 nm through highly anomalous dispersive photonic crystal fber. Opt. Exp. **19**(22), 21809–218011 (2011)
- Mohebbi, M.: Silicon photonic nanowire soliton-efect compressor at 1.5μm. IEEE Photonics Technol. Lett. **20**(11), 921–924 (2008)
- Mohebi, M., Khormai, H.: Efects of higher order dispersions on soliton-efect pulse compression in a silicon photonic nanowire. In: IEEE Conference (2011)
- Raja, R.V., Porsezian, K., Varshney, S.K.: Modeling photonic crystal fiber for efficient soliton pulse propagation at 850 nm. Sci. Direct **39**(5), 5000–5006 (2010)
- Saghaei, H., Ghanbari, A.: White light generation using photonic crystal fber with sub-micron circular lattice. J. Electr. Eng. **68**(4), 282–289 (2017)
- Saghaei, H.: Modeling and simulation of nonlinear effects in dispersion engineered photonic crystal fibers for supercontinuum generation. Ph.D. Thesis, Islamic Azad Univesrity, Science and Research Branch, Tehran (2015)
- Saghaei, H., Koohi-kamali, F., Ebnali-Heidari, M., Moravvej-Farshi, M.K.: Super-Continuum Generation in Photonic Crystal Fiber Using Selective Opto-Fluidic Infltration, pp. 106–110. ICOP, Tabriz (2012)
- Saghaei, H., Heidari, M.E., Farshi, K.M.: Mid infrared super-continuum generation via As2se3 chalcogenide photonic crystal fbers. Appl. Opt. J. **54**(8), 2072–2079 (2015)
- Yue, Y., Zhang, L., Huang, H.: Silicon-on-nitride waveguide with ultralow dispersion over an octave-spanning mid-infrared wavelength rang. IEEE Photonic J. **4**(1), 126–132 (2012)